74LVT16245B; 74LVTH16245B

3.3 V 16-bit transceiver; 3-state

Rev. 8 — 17 June 2011 Product data sheet

1. General description

The 74LVT16245B; 74LVTH16245B is a high-performance BiCMOS product designed for V_{CC} operation at 3.3 V.

This device is a 16-bit transceiver featuring non-inverting 3-state bus compatible outputs in both send and receive directions. The control function implementation minimizes external timing requirements. The device features an output enable input ($n\overline{OE}$) for easy cascading and a direction input (nDIR) for direction control.

2. Features and benefits

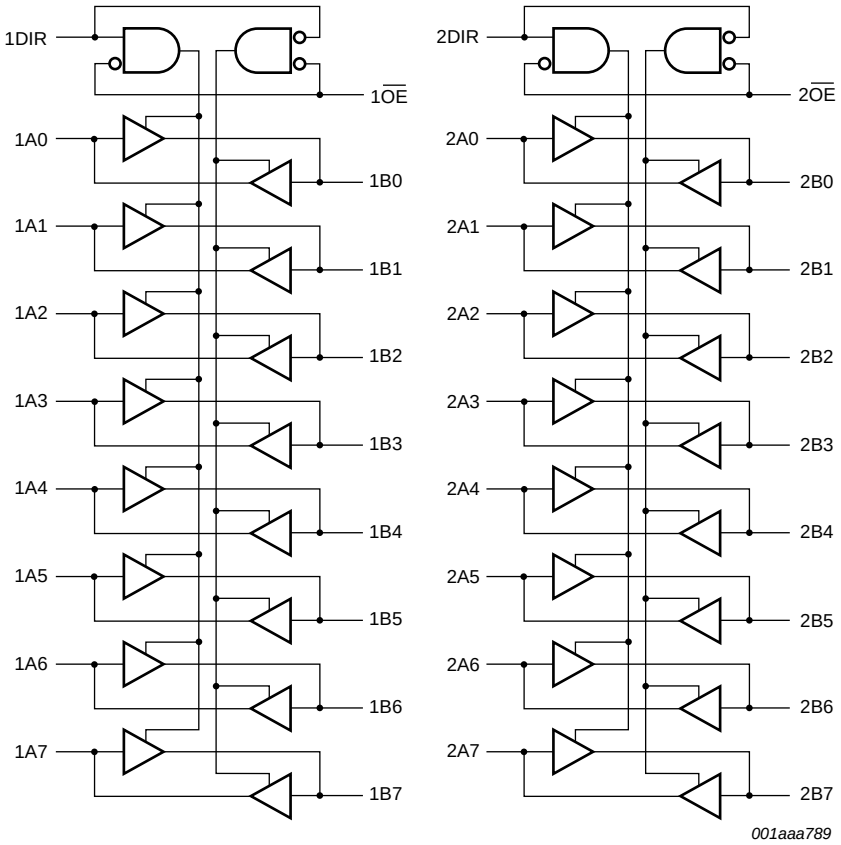
- 16-bit bidirectional bus interface
- 3-state buffers
- Output capability: +64 mA and −32 mA
- TTL input and output switching levels
- Input and output interface capability to systems at 5 V supply
- Bus hold data inputs eliminate need for external pull-up resistors to hold unused inputs
- Live insertion and extraction permitted
- Power-up 3-state
- No bus current loading when output is tied to 5 V bus
- Latch-up protection:
  - JESD78B Class II exceeds 500 mA
- ESD protection:
  - HBM JESD22-A114F exceeds 2000 V
  - MM JESD22-A115-A exceeds 200 V

3. Ordering information

Table 1. Ordering information

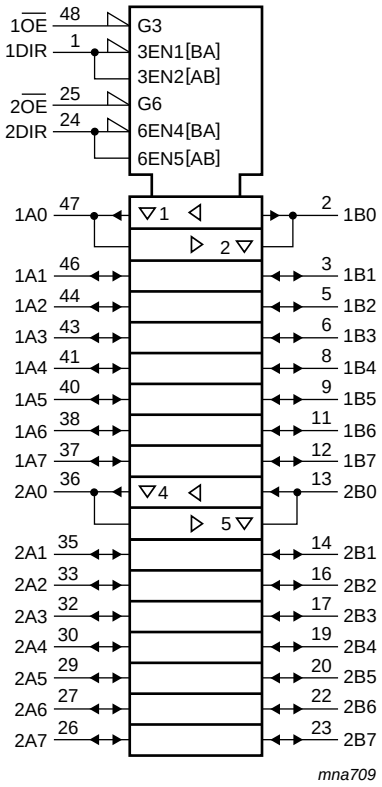
Type number	Package			
	Temperature range	Name	Description	Version
74LVT16245BDL	−40 °C to +85 °C	SSOP48	plastic shrink small outline package; 48 leads; body width 7.5 mm	SOT370-1
74LVTH16245BDL				
74LVT16245BDGG	−40 °C to +85 °C	TSSOP48	plastic thin shrink small outline package; 48 leads; body width 6.1 mm	SOT362-1
74LVTH16245BDGG				
74LVT16245BEV	−40 °C to +85 °C	VFBGA56	plastic very thin fine-pitch ball grid array package; 56 balls; body 4.5 × 7 × 0.65 mm	SOT702-1
74LVT16245BBX	−40 °C to +85 °C	HXQFN60U	plastic thermal enhanced extremely thin quad flat package; no leads; 60 terminals; UTLP based; body 4 × 6 × 0.5 mm	SOT1134-1
74LVTH16245BBX				

4. Functional diagram



Pin numbers are shown for SSOP48 and TSSOP48 packages only.

Fig 1. Logic symbol



Pin numbers are shown for SSOP48 and TSSOP48 packages only.

Fig 2. IEC logic symbol

5. Pinning information

5.1 Pinning

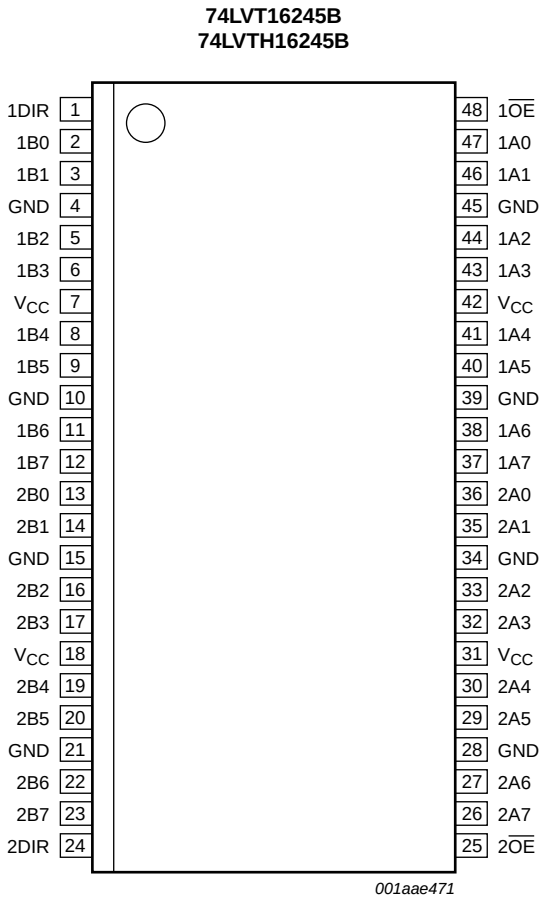


Fig 3. Pin configuration for SSOP48 and TSSOP48

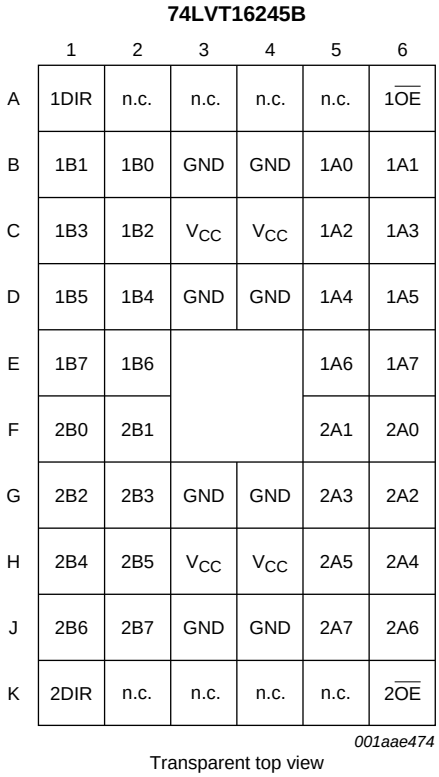
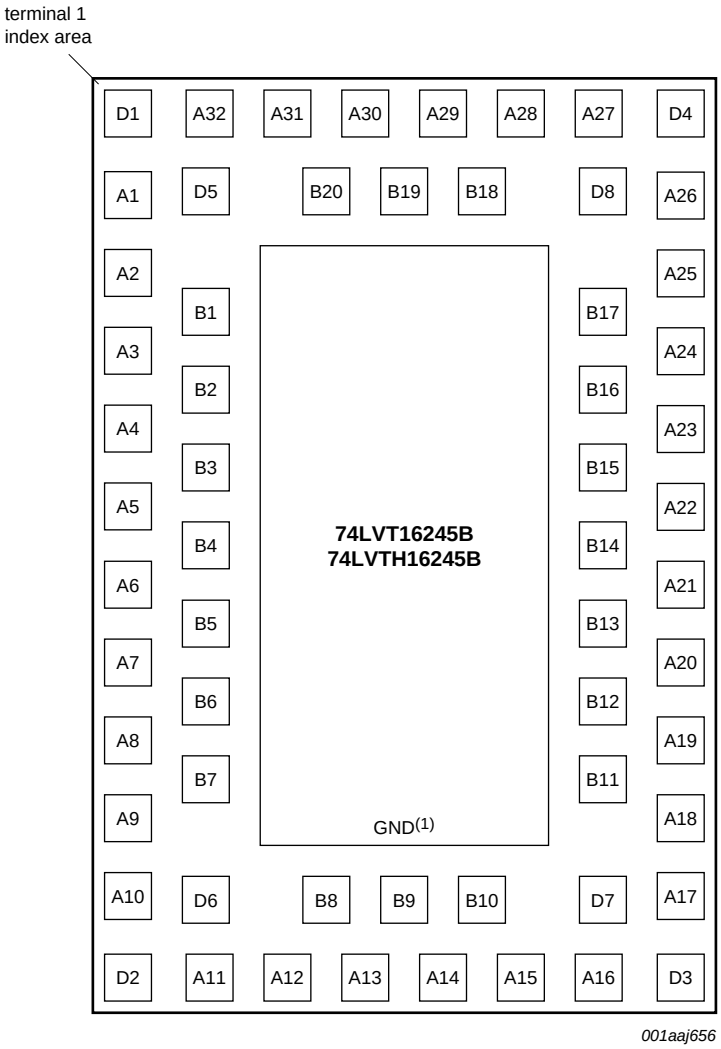


Fig 4. Pin configuration for VFBGA56



Transparent top view

(1) The die substrate is attached to this pad using conductive die attach material. It can not be used as a supply pin or input.

Fig 5. Pin configuration SOT1134-1 (HXQFN60U)

5.2 Pin description

Table 2. Pin description

Symbol	Pin			Description
	SOT370-1 and SOT362-1	SOT702-1	SOT1134-1	
1DIR, 2DIR	1, 24	A1, K1	A30, A13	direction control input
1B0 to 1B7	2, 3, 5, 6, 8, 9, 11, 12	B2, B1, C2, C1, D2, D1, E2, E1	B20, A31, D5, D1, A2, B2, B3, A5	data input/output
2B0 to 2B7	13, 14, 16, 17, 19, 20, 22, 23	F1, F2, G1, G2, H1, H2, J1, J2	A6, B5, B6, A9, D2, D6, A12, B8	data input/output
GND	4, 10, 15, 21, 28, 34, 39, 45	B3, D3, G3, J3, J4, G4, D4, B4	A32, A3, A8, A11, A16, A19, A24, A27	ground (0 V)
V_{CC}	7, 18, 31, 42	C3, H3, H4, C4	A1, A10, A17, A26	supply voltage
$1\overline{OE}$, $2\overline{OE}$	48, 25	A6, K6	A29, A14	output enable input (active LOW)
2A0 to 2A7	36, 35, 33, 32, 30, 29, 27, 26	F6, F5, G6, G5, H6, H5, J6, J5	A21, B13, B12, A18, D3, D7, A15, B10	data input/output
1A0 to 1A7	47, 46, 44, 43, 41, 40, 38, 37	B5, B6, C5, C6, D5, D6, E5, E6	B18, A28, D8, D4, A25, B16, B15, A22	data input/output
n.c.	-	A2, A3, A4, A5, K2, K3, K4, K5	A4, A7, A20, A23, B1, B4, B7, B9, B11, B14, B17, B19	not connected

6. Functional description

6.1 Function table

Table 3. Function table [1]

Control		Input/output	
$n\overline{OE}$	nDIR	nAn	nBn
L	L	output nAn = nBn	input
L	H	input	output nBn = nAn
H	X	Z	Z

[1] H = HIGH voltage level;
L = LOW voltage level;
X = don't care;
Z = high-impedance OFF-state.

7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{CC}	supply voltage			−0.5	+4.6	V
V_I	input voltage		[1]	−0.5	+7.0	V
V_O	output voltage	output in OFF-state or HIGH-state	[1]	−0.5	+7.0	V
I_{IK}	input clamping current	$V_I < 0$ V		−50	-	mA
I_{OK}	output clamping current	$V_O < 0$ V		−50	-	mA
I_O	output current	output in LOW-state		-	128	mA
		output in HIGH-state		−64	-	mA
T_{stg}	storage temperature			−65	+150	°C
T_j	junction temperature		[2]	-	150	°C
P_{tot}	total power dissipation	T_{amb} = −40 °C to +85 °C;				
		(T)SSOP48 package	[3]	-	500	mW
		VFBGA56 package	[4]	-	1000	mW
		HXQFN60U package	[4]	-	1000	mW

[1] The input and output negative voltage ratings may be exceeded if the input and output clamp current ratings are observed.

[2] The performance capability of a high-performance integrated circuit in conjunction with its thermal environment can create junction temperatures which are detrimental to reliability.

[3] Above 60 °C the value of P_{tot} derates linearly with 5.5 mW/K.

[4] Above 70 °C the value of P_{tot} derates linearly with 1.8 mW/K.

8. Recommended operating conditions

Table 5. Recommended operating conditions

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{CC}	supply voltage		2.7	-	3.6	V
V_I	input voltage		0	-	5.5	V
V_{IH}	HIGH-level input voltage		2.0	-	-	V
V_{IL}	LOW-level input voltage		-	-	0.8	V
I_{OH}	HIGH-level output current		−32	-	-	mA
I_{OL}	LOW-level output current	none	-	-	32	mA
		current duty cycle ≤ 50 %; $f_i \geq 1$ kHz	-	-	64	mA
T_{amb}	ambient temperature	in free-air	−40	-	+85	°C
$\Delta t/\Delta V$	input transition rise and fall rate	outputs enabled	-	-	10	ns/V

9. Static characteristics

Table 6. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
T_{amb} = –40 °C to +85 °C [1]							
V_{IK}	input clamping voltage	V_{CC} = 2.7 V; I_{IK} = –18 mA		–1.2	–0.85	-	V
V_{OH}	HIGH-level output voltage	I_{OH} = –100 µA; V_{CC} = 2.7 V to 3.6 V		V_{CC} – 0.2	V_{CC}	-	V
		I_{OH} = –8 mA; V_{CC} = 2.7 V		2.4	2.5	-	V
		I_{OH} = –32 mA; V_{CC} = 3.0 V		2.0	2.3	-	V
V_{OL}	LOW-level output voltage	V_{CC} = 2.7 V					
		I_{OL} = 100 µA		-	0.07	0.2	V
		I_{OL} = 24 mA		-	0.3	0.5	V
		V_{CC} = 3.0 V					
		I_{OL} = 16 mA		-	0.25	0.4	V
		I_{OL} = 32 mA		-	0.3	0.5	V
		I_{OL} = 64 mA		-	0.4	0.55	V
I_I	input leakage current	control pins					
		V_{CC} = 3.6 V; V_I = V_{CC} or GND		-	0.1	±1	µA
		V_{CC} = 0 V or 3.6 V; V_I = 5.5 V		-	0.1	10	µA
		input/output data pins; V_{CC} = 3.6 V	[2]				
		V_I = 5.5 V		-	0.1	20	µA
		V_I = V_{CC}		-	0.5	10	µA
		V_I = 0 V		–5	–0.1	-	µA
I_{OFF}	power-off leakage current	V_{CC} = 0 V; V_I or V_O = 0 V to 4.5 V		-	0.1	±100	µA
I_{BHL}	bus hold LOW current	V_{CC} = 3 V; V_I = 0.8 V	[3]	75	135	-	µA
I_{BHH}	bus hold HIGH current	V_{CC} = 3 V; V_I = 2.0 V		-	–135	–75	µA
I_{BHLO}	bus hold LOW overdrive current	nAn input; V_I = 0 V to 3.6 V; V_{CC} = 3.6 V		500	-	-	µA
I_{BHHO}	bus hold HIGH overdrive current	nAn input; V_I = 0 V to 3.6 V; V_{CC} = 3.6 V		-	-	–500	µA
I_{LO}	output leakage current	output in HIGH-state when V_O > V_{CC}; V_O = 5.5 V; V_{CC} = 3.0 V		-	75	125	µA
$I_{O(pu/pd)}$	power-up/power-down output current	V_{CC} ≤ 1.2 V; V_O = 0.5 V to V_{CC}; V_I = GND or V_{CC}; $n\overline{OE}$ = don't care	[4]	-	40	±100	µA
I_{CC}	supply current	V_{CC} = 3.6 V; V_I = GND or V_{CC}; I_O = 0 A					
		outputs HIGH		-	0.07	0.12	mA
		outputs LOW		-	4.7	6.0	mA
		outputs disabled	[5]	-	0.07	0.12	mA
ΔI_{CC}	additional supply current	per input pin; V_{CC} = 3.0 V to 3.6 V; one input at V_{CC} – 0.6 V, other inputs at V_{CC} or GND	[6]	-	0.1	0.2	mA
C_I	input capacitance	pins nDIR and $n\overline{OE}$, V_O = 0 V or 3.0 V		-	3	-	pF

Table 6. Static characteristics *...continued*

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$C_{io(off)}$	off-state input/output capacitance	pins nAn and nBn, outputs disabled; V_O = GND or V_{CC}	-	9	-	pF

[1] Typical values are measured at V_{CC} = 3.3 V and at T_{amb} = 25 °C.

[2] Unused pins at V_{CC} or GND.

[3] This is the bus hold overdrive current required to force the input to the opposite logic state.

[4] This parameter is valid for any V_{CC} between 0 V and 1.2 V with a transition time of up to 10 ms. From V_{CC} = 1.2 V to V_{CC} = 3.3 V ± 0.3 V a transition time of 100 μs is permitted. This parameter is valid for T_{amb} = 25 °C only.

[5] I_{CC} is measured with outputs pulled to V_{CC} or GND.

[6] This is the increase in supply current for each input at the specified voltage level other than V_{CC} or GND.

10. Dynamic characteristics

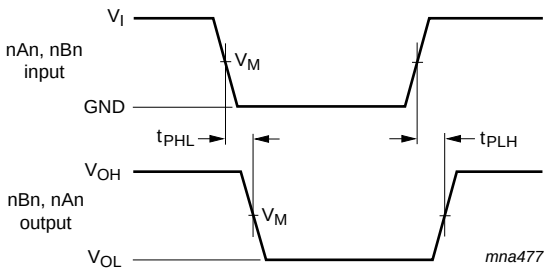
Table 7. Dynamic characteristics

Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 8.

Symbol	Parameter	Conditions	Min	Typ[1]	Max	Unit
T_{amb} = –40 °C to +85 °C						
t_{PLH}	LOW to HIGH propagation delay	nAn to nBn or nBn to nAn; see Figure 6				
		V_{CC} = 2.7 V	-	-	3.5	ns
		V_{CC} = 3.0 V to 3.6 V	1.0	1.9	3.3	ns
t_{PHL}	HIGH to LOW propagation delay	nAn to nBn or nBn to nAn; see Figure 6				
		V_{CC} = 2.7 V	-	-	3.5	ns
		V_{CC} = 3.0 V to 3.6 V	1.0	1.7	3.3	ns
t_{PZH}	OFF-state to HIGH propagation delay	$n\overline{OE}$ to nAn or nBn; see Figure 7				
		V_{CC} = 2.7 V	-	-	5.3	ns
		V_{CC} = 3.0 V to 3.6 V	1.0	2.8	4.5	ns
t_{PZL}	OFF-state to LOW propagation delay	$n\overline{OE}$ to nAn or nBn; see Figure 7				
		V_{CC} = 2.7 V	-	-	5.1	ns
		V_{CC} = 3.0 V to 3.6 V	1.0	2.8	4.1	ns
t_{PHZ}	HIGH to OFF-state propagation delay	$n\overline{OE}$ to nAn or nBn; see Figure 7				
		V_{CC} = 2.7 V	-	-	5.7	ns
		V_{CC} = 3.0 V to 3.6 V	1.5	3.2	5.1	ns
t_{PLZ}	LOW to OFF-state propagation delay	$n\overline{OE}$ to nAn or nBn; see Figure 7				
		V_{CC} = 2.7 V	-	-	4.6	ns
		V_{CC} = 3.0 V to 3.6 V	1.5	3.0	4.6	ns

[1] All typical values are at V_{CC} = 3.3 V and T_{amb} = 25 °C.

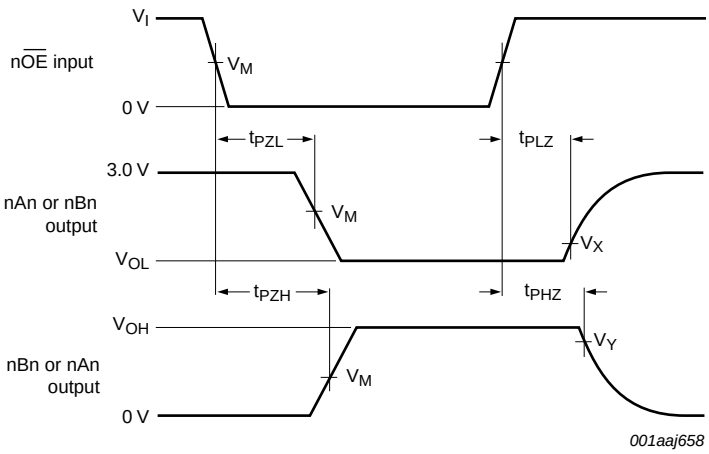
11. Waveforms



Measurements points are given in Table 8.

V_{OL} and V_{OH} are typical voltage output levels that occur with the output load.

Fig 6. Propagation delay input (nAn, nBn) to output (nBn, nAn)



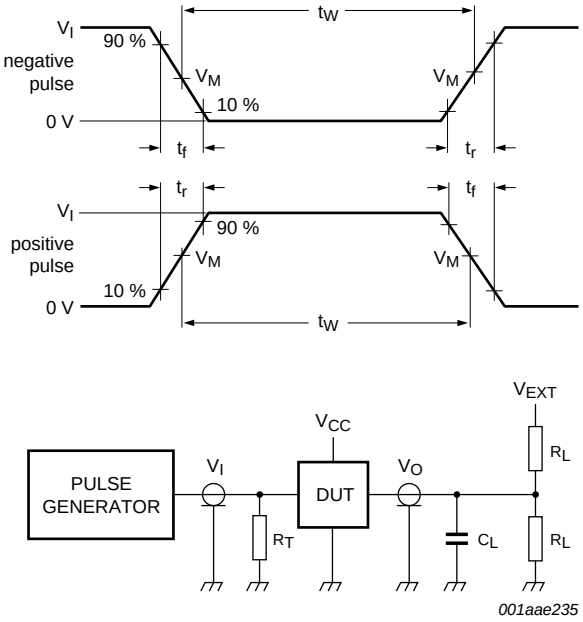
Measurements points are given in Table 8.

V_{OL} and V_{OH} are typical voltage output levels that occur with the output load.

Fig 7. 3-state output enable and disable times

Table 8. Measurement points

Input	Output		
V_M	V_M	V_X	V_Y
1.5 V	1.5 V	V_{OL} + 0.3 V	V_{OH} − 0.3 V



Test data is given in Table 9.

Definitions test circuit:

R_L = Load resistance.

C_L = Load capacitance including jig and probe capacitance.

R_T = Termination resistance should be equal to output impedance Z_o of the pulse generator.

V_{EXT} = External voltage for measuring switching times.

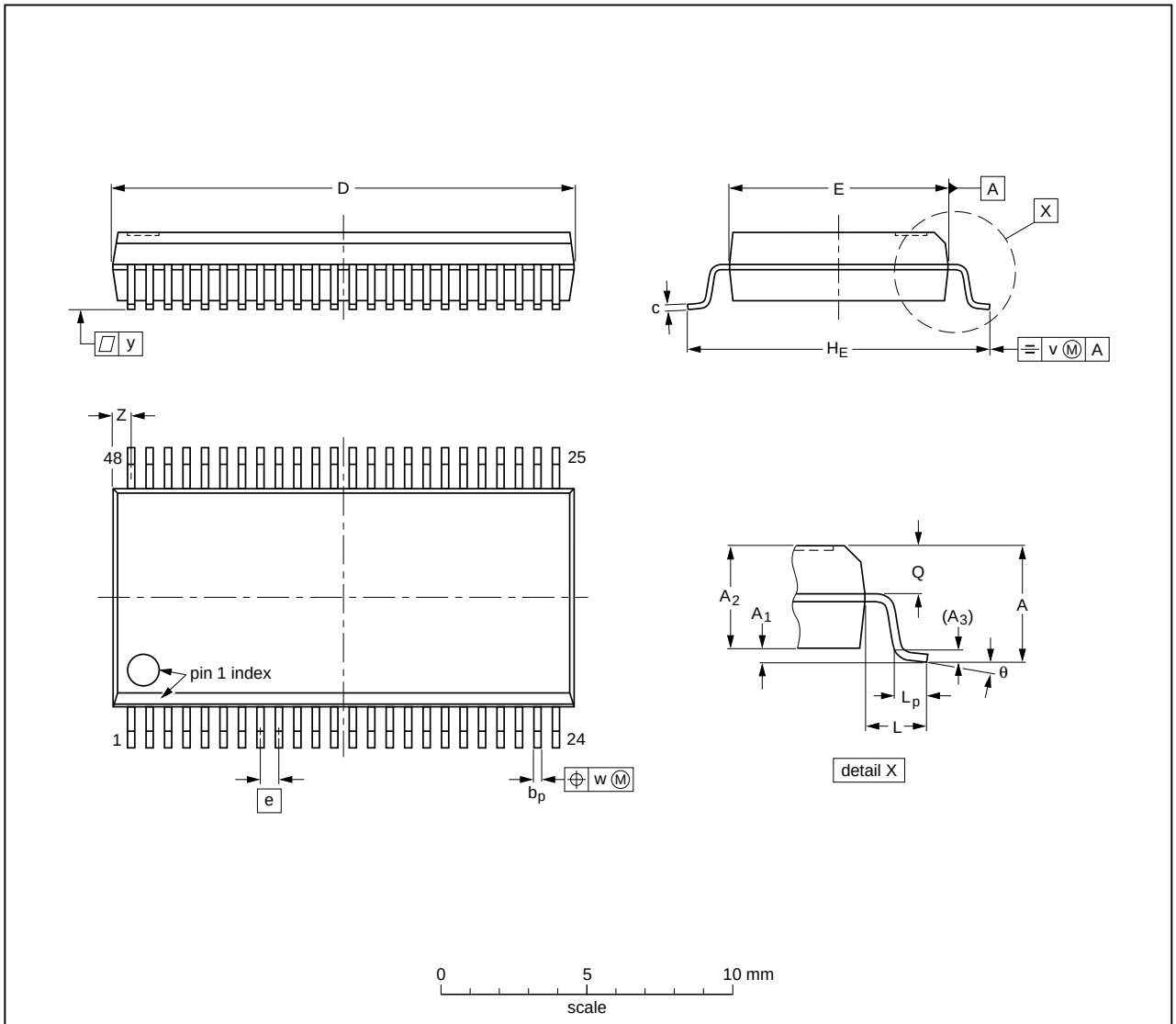
Fig 8. Test circuit for measuring switching times

Table 9. Test data

Input				Load		V_{EXT}		
V_I	f_i	t_W	t_r, t_f	C_L	R_L	t_{PHZ}, t_{PZH}	t_{PLZ}, t_{PZL}	t_{PLH}, t_{PHL}
2.7 V	≤ 10 MHz	500 ns	≤ 2.5 ns	50 pF	500 Ω	GND	6 V	open

12. Package outline

SSOP48: plastic shrink small outline package; 48 leads; body width 7.5 mm **SOT370-1**



DIMENSIONS (mm are the original dimensions)

UNIT	A max.	A_1	A_2	A_3	b_p	c	D (1)	E (1)	e	H_E	L	L_p	Q	v	w	y	Z (1)	θ
mm	2.8	0.4 0.2	2.35 2.20	0.25	0.3 0.2	0.22 0.13	16.00 15.75	7.6 7.4	0.635	10.4 10.1	1.4	1.0 0.6	1.2 1.0	0.25	0.18	0.1	0.85 0.40	8^o 0^o

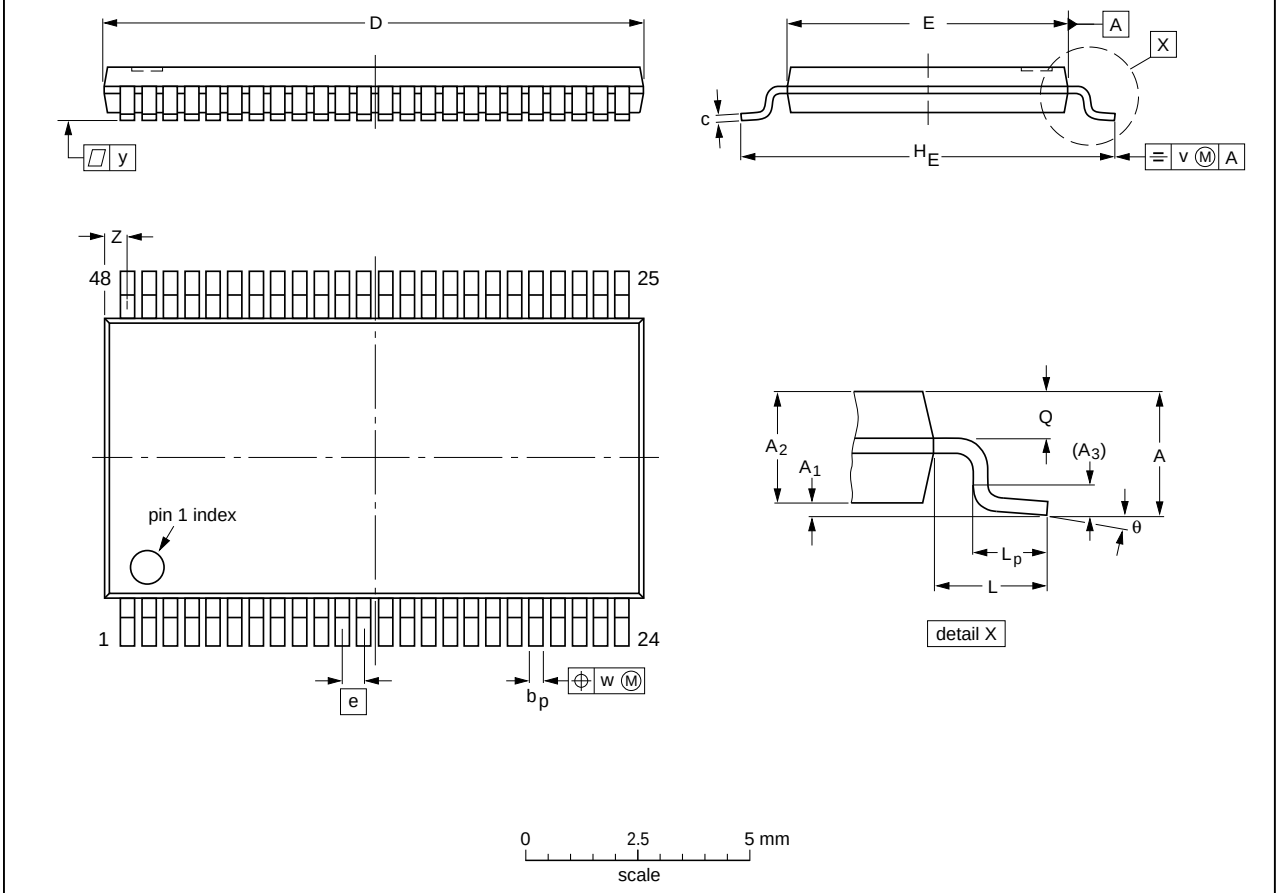
Note

1. Plastic or metal protrusions of 0.25 mm maximum per side are not included.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT370-1		MO-118				~~99-12-27~~ 03-02-19

Fig 9. Package outline SOT370-1 (SSOP48)

TSSOP48: plastic thin shrink small outline package; 48 leads; body width 6.1 mm **SOT362-1**



DIMENSIONS (mm are the original dimensions).

UNIT	A max.	A_1	A_2	A_3	b_p	c	$D^{(1)}$	$E^{(2)}$	e	H_E	L	L_p	Q	v	w	y	Z	θ
mm	1.2	0.15 0.05	1.05 0.85	0.25	0.28 0.17	0.2 0.1	12.6 12.4	6.2 6.0	0.5	8.3 7.9	1	0.8 0.4	0.50 0.35	0.25	0.08	0.1	0.8 0.4	8^o 0^o

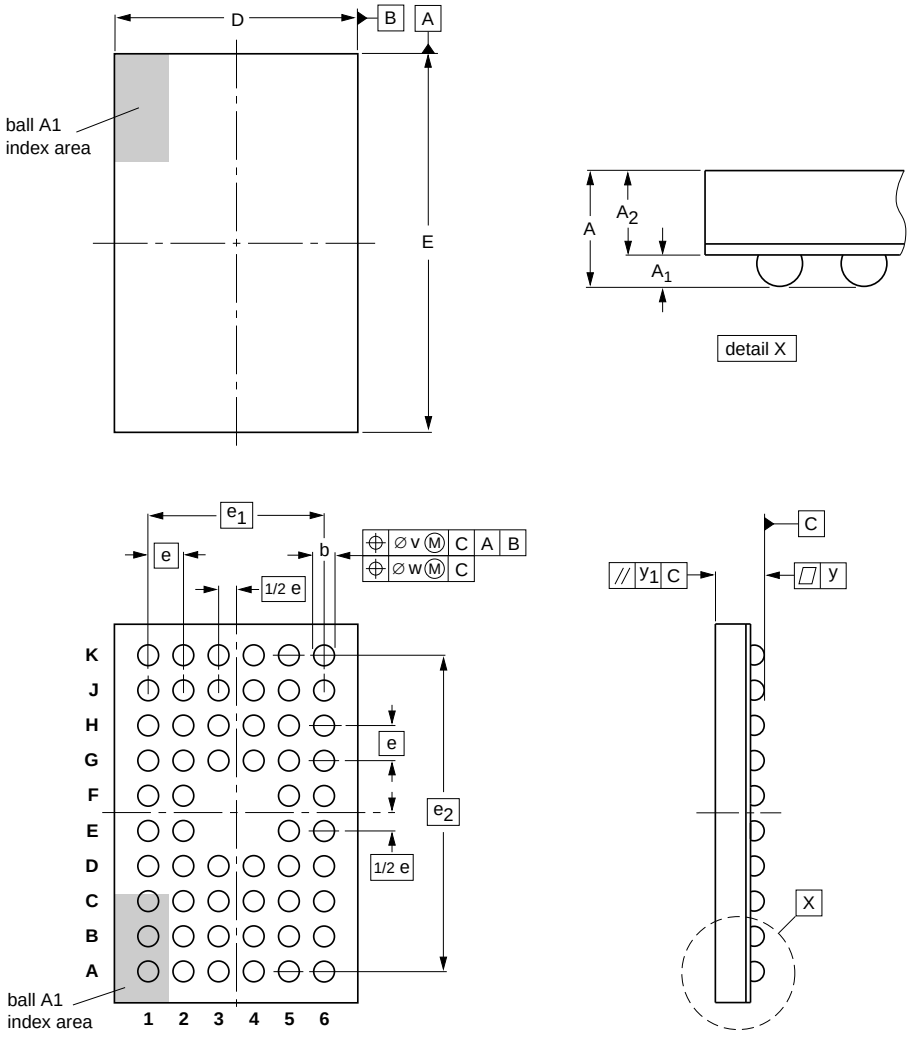
Notes

1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.
2. Plastic interlead protrusions of 0.25 mm maximum per side are not included.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT362-1		MO-153				~~99-12-27~~ 03-02-19

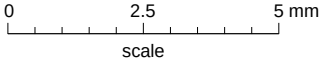
Fig 10. Package outline SOT362-1 (TSSOP48)

VFBGA56: plastic very thin fine-pitch ball grid array package; 56 balls; body 4.5 x 7 x 0.65 mm **SOT702-1**



DIMENSIONS (mm are the original dimensions)

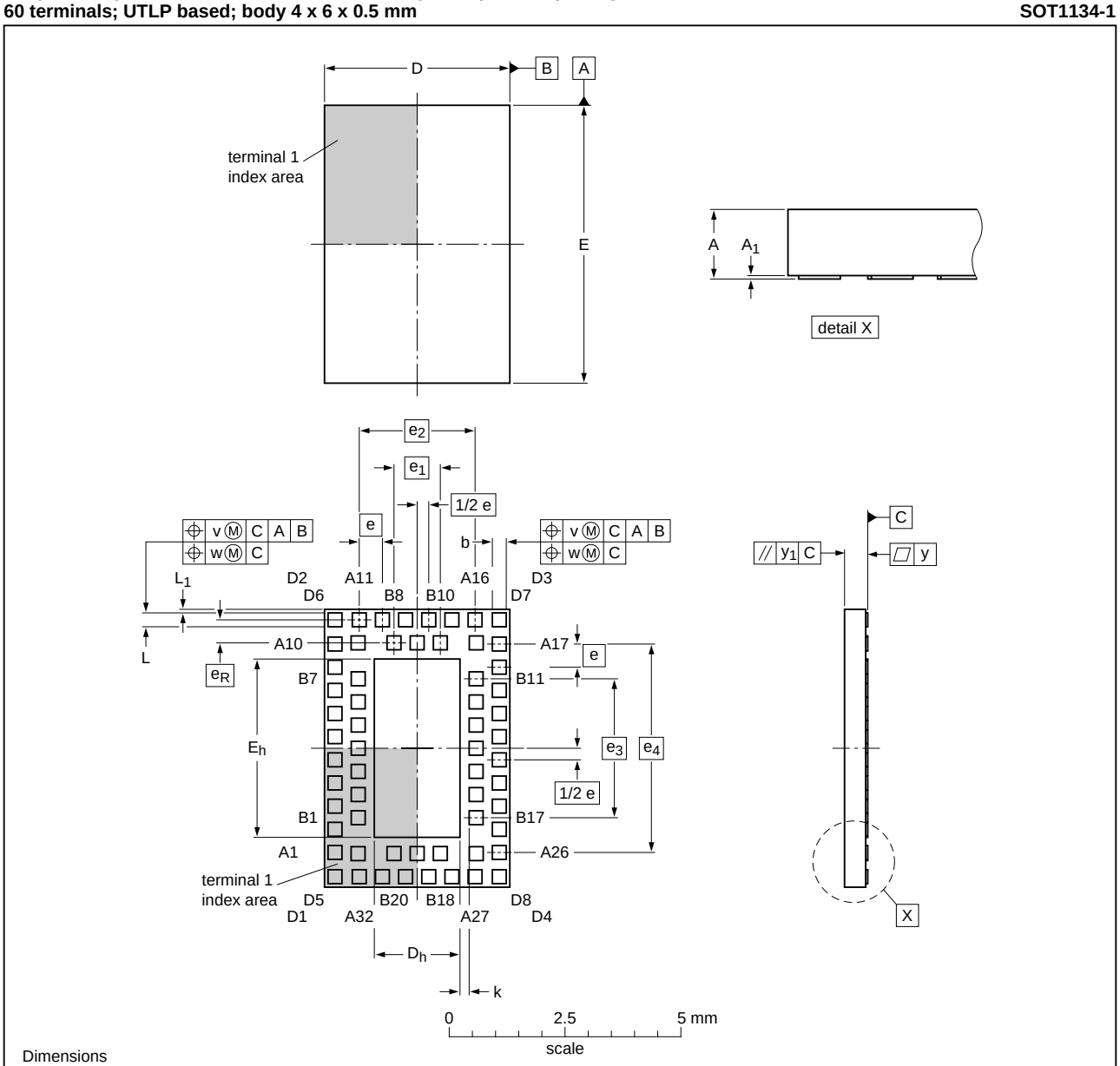
UNIT	A max.	A_1	A_2	b	D	E	e	e_1	e_2	v	w	y	y_1
mm	1	0.3 0.2	0.7 0.6	0.45 0.35	4.6 4.4	7.1 6.9	0.65	3.25	5.85	0.15	0.08	0.08	0.1



OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT702-1		MO-225				~~02-08-08~~ 03-07-01

Fig 11. Package outline SOT702-1 (VFBGA56)

HXQFN60U: plastic thermal enhanced extremely thin quad flat package; no leads; 60 terminals; UTLP based; body 4 x 6 x 0.5 mm **SOT1134-1**



Dimensions

Unit		A	A_1	b	D	D_h	E	E_h	e	e_1	e_2	e_3	e_4	eR	k	L	L_1	v	w	y	y_1
mm	max	0.50	0.05	0.35	4.1	1.90	6.1	3.90							0.25	0.35	0.125				
	nom	0.48	0.02	0.30	4.0	1.85	6.0	3.85	0.5	1	2.5	3	4.5	0.5	0.20	0.30	0.075	0.07	0.05	0.08	0.1
	min	0.46	0.00	0.25	3.9	1.80	5.9	3.80							0.15	0.25	0.025				

sot1134-1_po

Outline version	References				European projection	Issue date
	IEC	JEDEC	JEITA			
SOT1134-1	- - -	- - -	- - -			~~08-12-17~~ 09-01-22

Fig 12. Package outline SOT1134-1 (HXQFN60U)

13. Abbreviations

Table 10. Abbreviations

Acronym	Description
BiCMOS	Bipolar Complementary Metal Oxide Semiconductor
DUT	Device Under Test
ESD	ElectroStatic Discharge
HBM	Human Body Model
MM	Machine Model
TTL	Transistor-Transistor Logic

14. Revision history

Table 11. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74LVT_LVTH16245B v.8	20110617	Product data sheet	-	74LVT_LVTH16245B v.7
Modifications:	• 74LVT16245BBQ and 74LVTH16245BBQ changed to 74LVT16245BBX and 74LVTH16245BBX for HXQFN60U (SOT1134-1) package.			
74LVT_LVTH16245B v.7	20100329	Product data sheet	-	74LVT_LVTH16245B v.6
Modifications:	• 74LVT16245BBQ and 74LVTH16245BBQ changed from HUQFN60U (SOT1025-1) to HXQFN60U (SOT1134-1) package.			
74LVT_LVTH16245B v.6	20090409	Product data sheet	-	74LVT_LVTH16245B v.5
74LVT_LVTH16245B v.5	20090312	Product data sheet	-	74LVT_LVTH16245B v.4
74LVT_LVTH16245B v.4	20060323	Product data sheet	-	74LVT16245B v.3
74LVT16245B v.3	20021031	Product data sheet	-	74LVT16245B v.2
74LVT16245B v.2	19980219	Product specification	-	74LVT16245B v.1
74LVT16245B v.1	19940523	Product specification	-	-

15. Legal information

15.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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17. Contents

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